

United States Patent [19]
Strumpell

[11] **Des. 262,962**
[45] **** Feb. 9, 1982**

[54] **SILICON WAFER EMITTER ELECTRODE CONFIGURATION**

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[**] Term: **14 Years**

[21] Appl. No.: **957,770**

[22] Filed: **Nov. 3, 1978**

[51] Int. Cl. **D13—99**

[52] U.S. Cl. **D13/99**

[58] Field of Search 437/77, 88, 93; 357/68, 357/70; D13/99

[56] **References Cited**

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[57] **CLAIM**

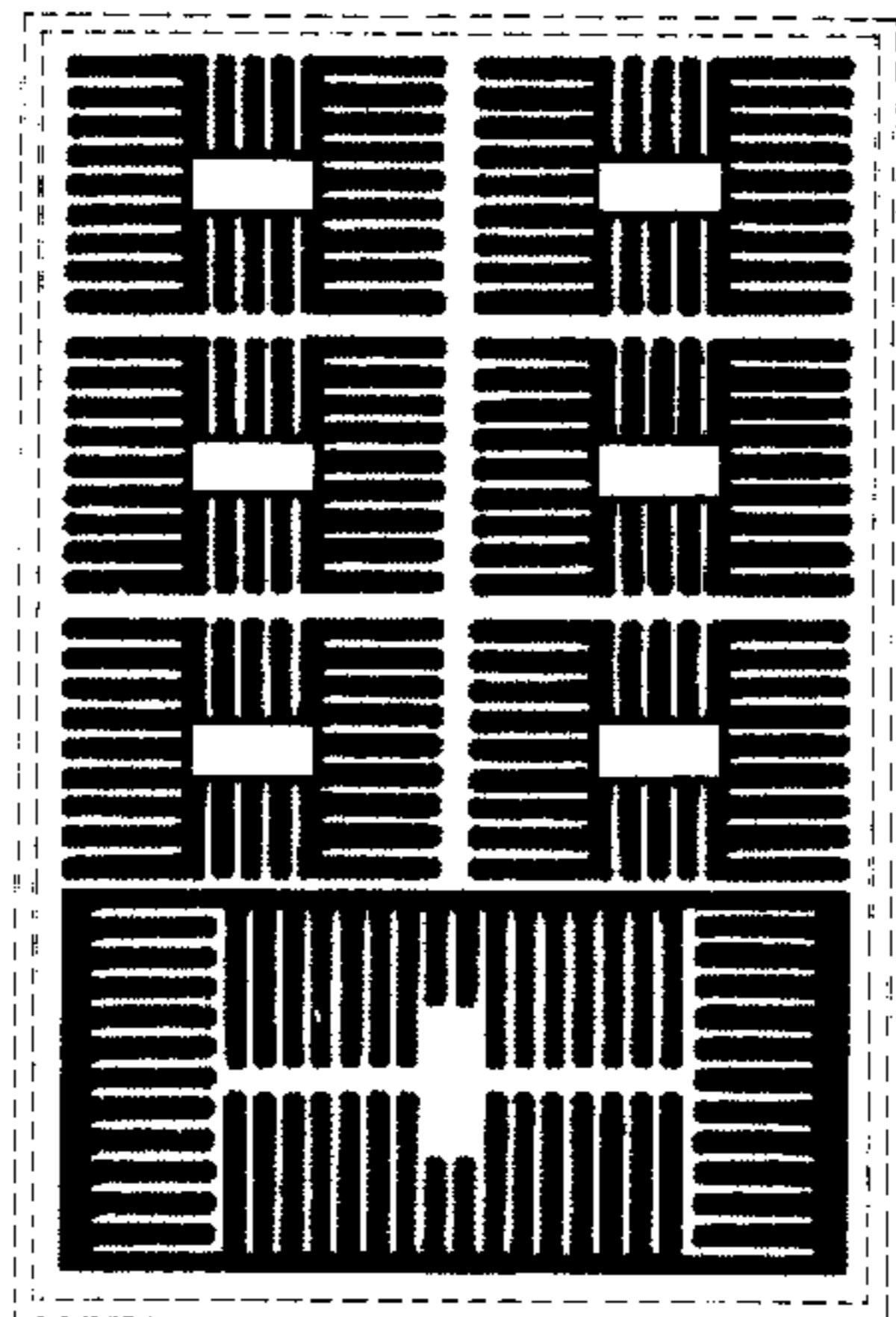
The ornamental design for a silicon wafer emitter electrode configuration, substantially as shown and described.

DESCRIPTION

FIG. 1 is a top plan view of a silicon wafer emitter electrode configuration showing my new design.

FIGS. 2 and 3 are end and side elevational views respectively of the electrode configuration.

This is a design for the characteristic features of emitter electrode configurations deposited on a silicon wafer with the electrodes delineated by the black areas in FIG. 1. The wafer is shown in broken lines for illustration purposes only.



U.S. Patent

Feb. 9, 1982

Des. 262,962

Fig. 2.

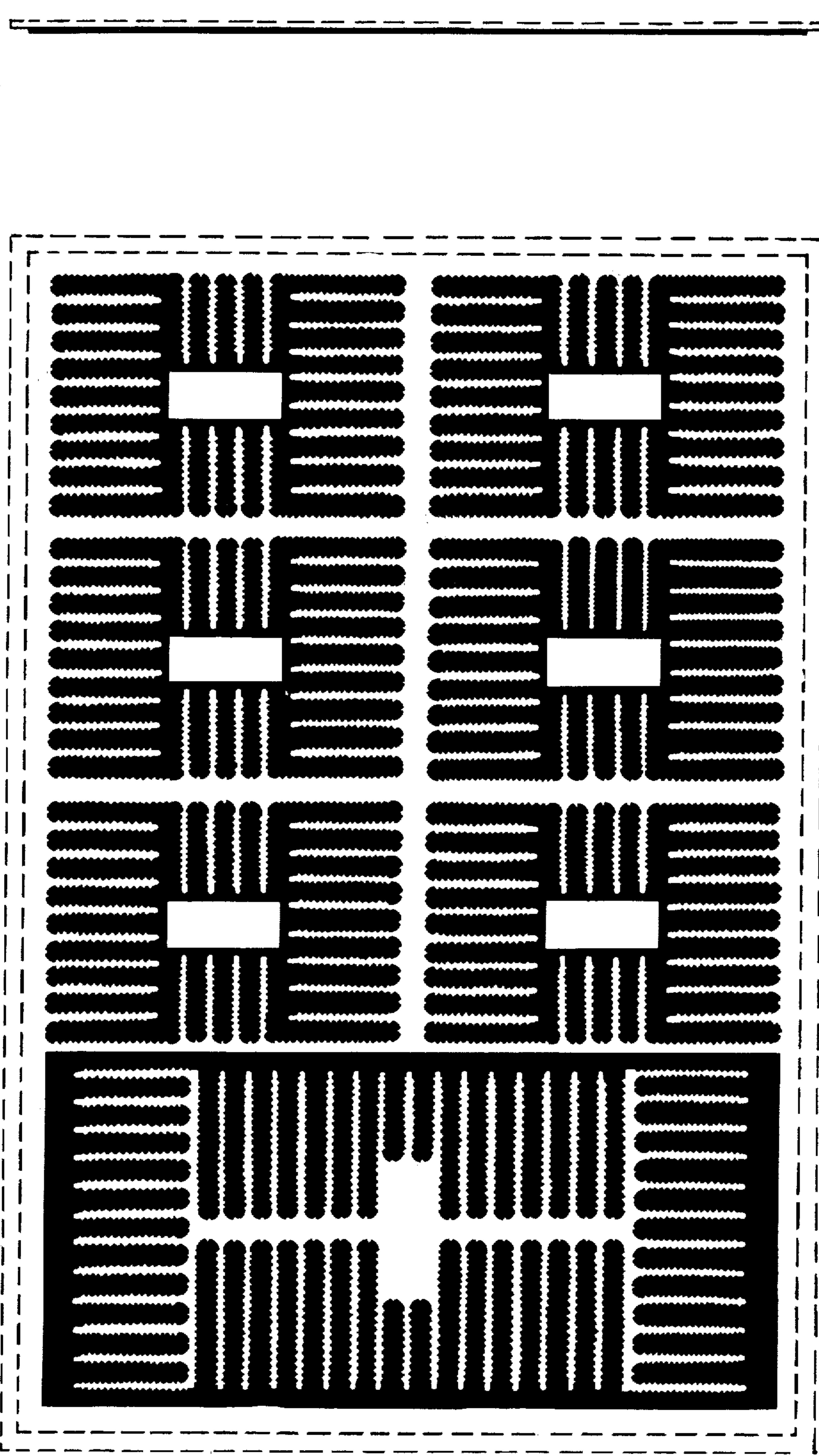


Fig. 1.

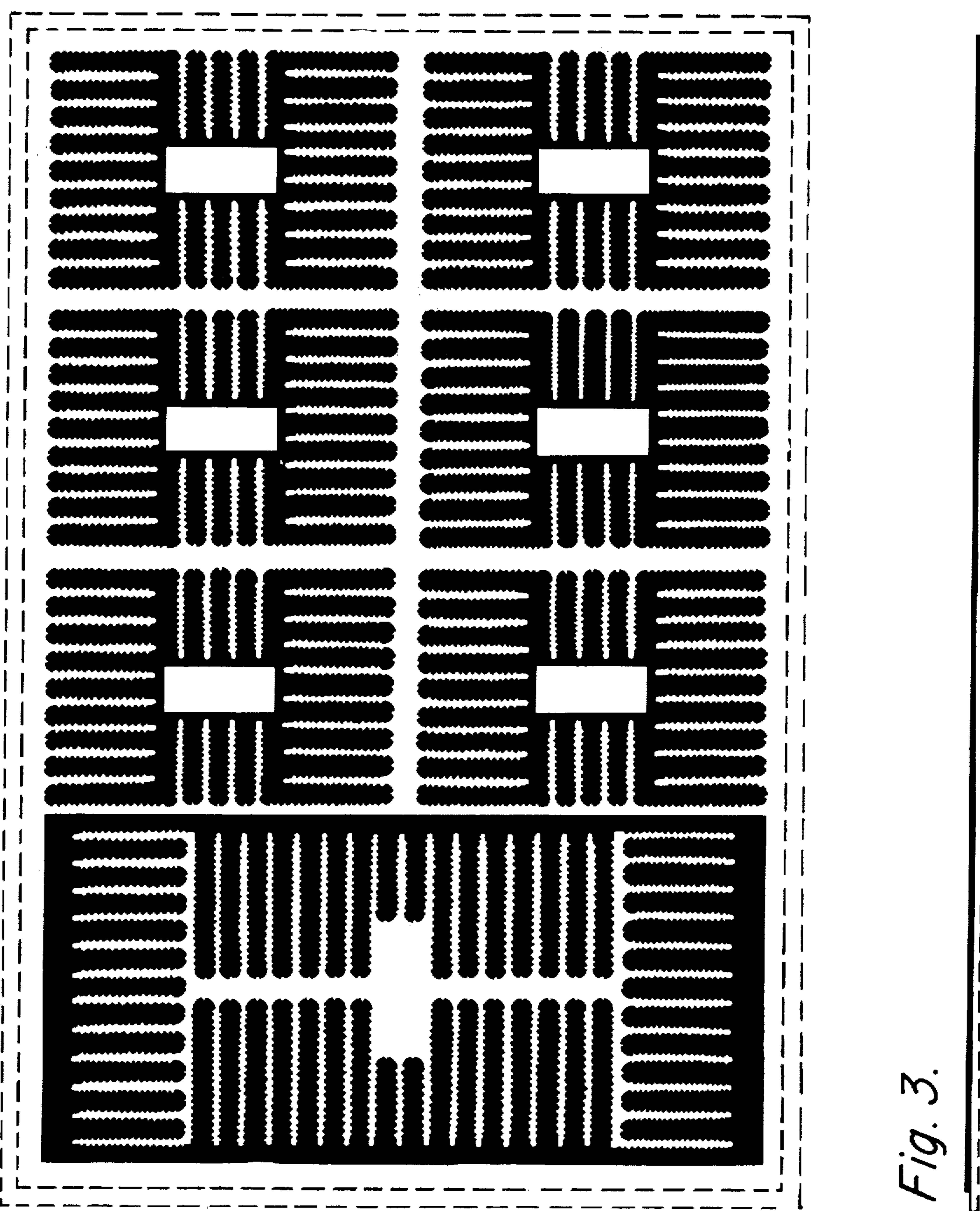


Fig. 3.